

What is claimed is:

SWP
A27
1. A semiconductor wafer with very small dot marks on an inner wall face of a notch formed on an outer peripheral face thereof, wherein the dot marks are formed by irradiating a laser beam having a diameter of 1 to 13 μm .

2. The semiconductor wafer according to Claim 1, wherein upper and lower edge line portions of the inner wall face of the notch are respectively chamfered to thereby constitute inclined faces and the dot marks are formed on the inclined faces.

3. The semiconductor wafer according to Claim 2, wherein an angle of an inclination of the inclined face relative to the surface of the semiconductor wafer is equal to or smaller than 30 degree.

4. The semiconductor wafer according to Claim 2, wherein a surface roughness of the inclined face is equal to or smaller than 1 μm .

5. The semiconductor wafer according to Claim 2, wherein the dot marks are formed at least either of the upper and lower inclined faces.

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